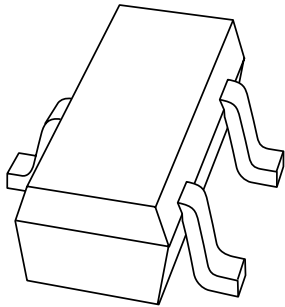


# DATA SHEET



## **PDT C114ES** NPN resistor-equipped transistor

Product specification  
Supersedes data of 1998 May 18

1998 Nov 26

# NPN resistor-equipped transistor

# PDTC114ES

### FEATURES

- Built-in bias resistors R1 and R2 (typ. 10 kΩ each)
- Simplification of circuit design
- Reduces number of components and board space.

### APPLICATIONS

- Especially suitable for space reduction in interface and driver circuits
- Inverter circuit configurations without use of external resistors.

### DESCRIPTION

NPN resistor-equipped transistor in a TO-92; SOT54 plastic package.  
PNP complement: PDTA114ES.

### PINNING

PIN	DESCRIPTION
1	base/input
2	collector/output
3	emitter/ground

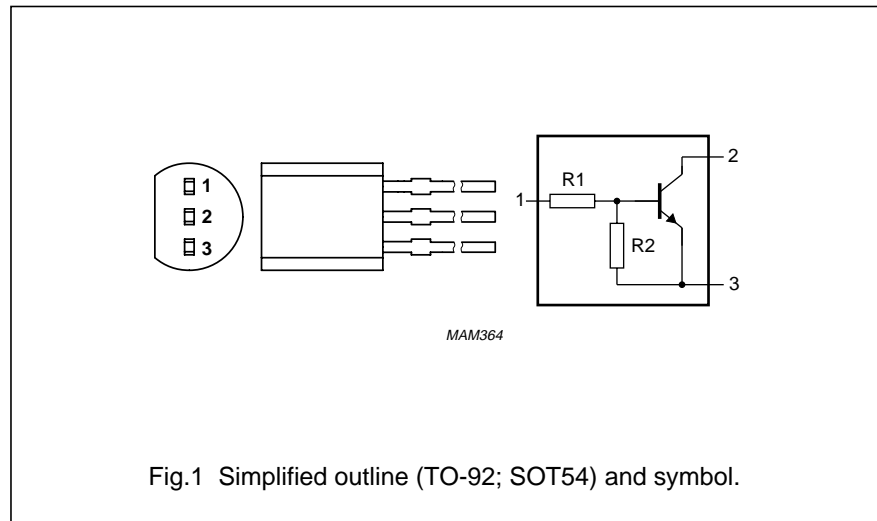


Fig.1 Simplified outline (TO-92; SOT54) and symbol.

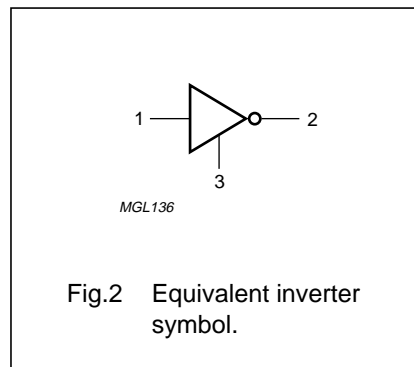


Fig.2 Equivalent inverter symbol.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CE0}$	collector-emitter voltage	open base	–	–	50	V
$I_O$	output current (DC)		–	–	100	mA
$I_{CM}$	peak collector current		–	–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	–	500	mW
$h_{FE}$	DC current gain	$I_C = 5\text{ mA}; V_{CE} = 5\text{ V}$	30	–	–	
R1	input resistor		7	10	13	kΩ
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	

## NPN resistor-equipped transistor

## PDTC114ES

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	50	V
$V_{CEO}$	collector-emitter voltage	open base	–	50	V
$V_{EBO}$	emitter-base voltage	open collector	–	10	V
$V_i$	input voltage		–	+40	V
			–	–10	V
$I_O$	output current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	100	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	500	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

**Note**

1. Transistor mounted on an FR4 printed-circuit board.

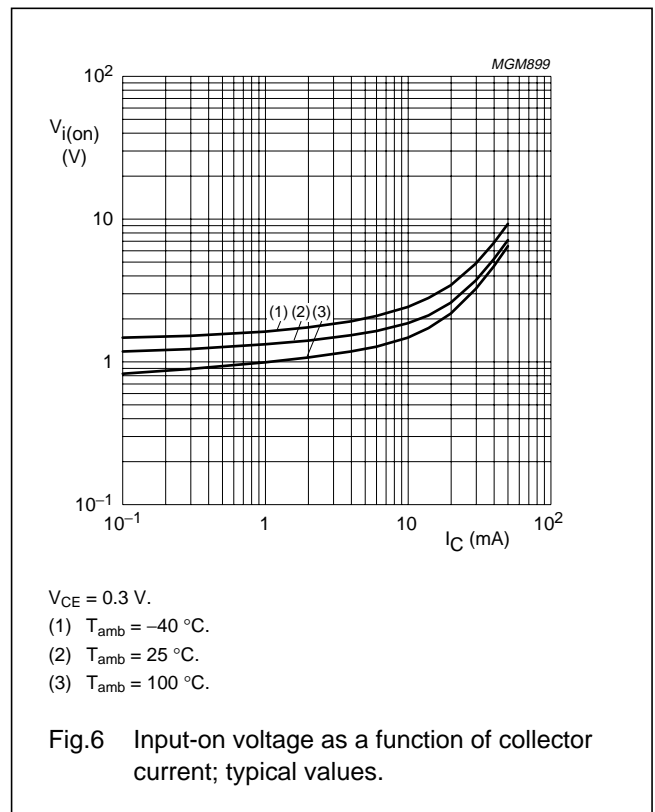
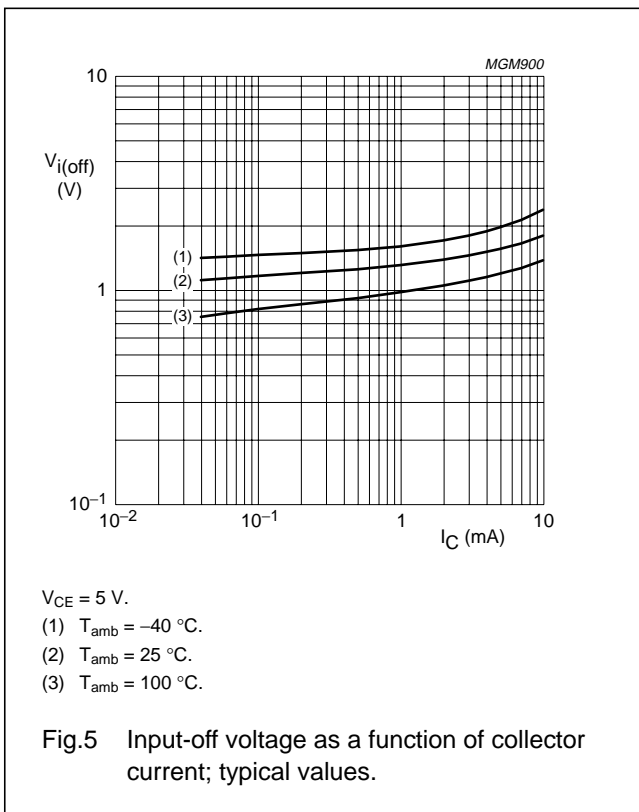
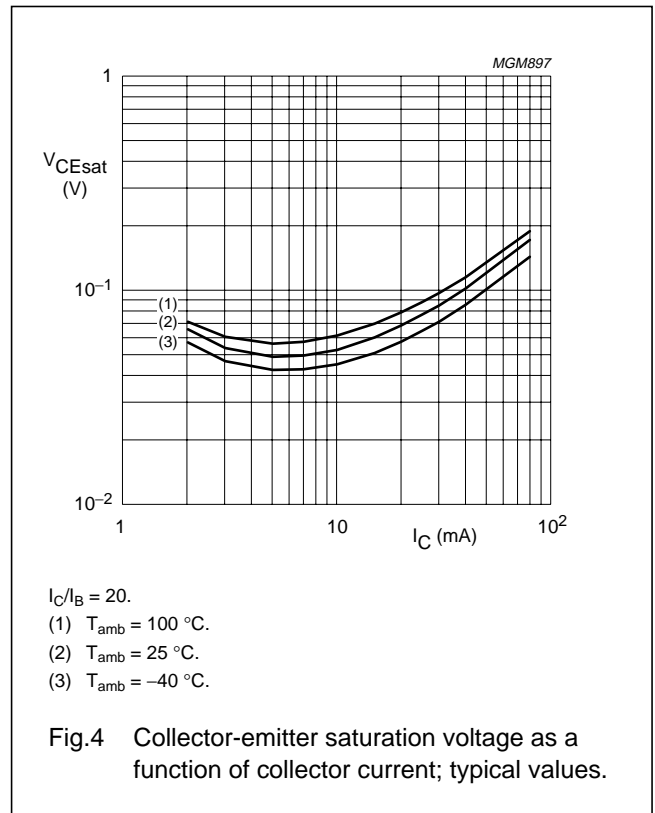
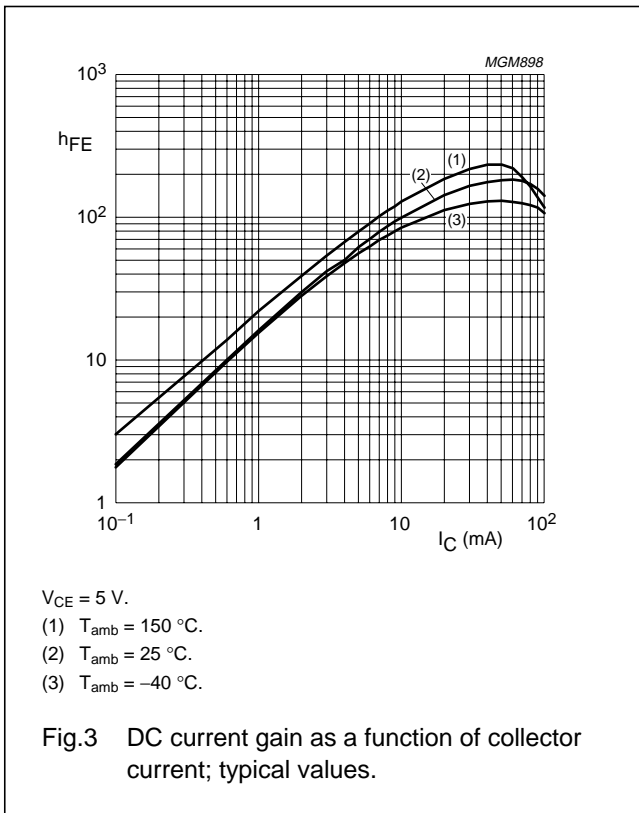
**CHARACTERISTICS**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0$ ; $V_{CB} = 50\text{ V}$	–	–	100	nA
$I_{CEO}$	collector cut-off current	$I_B = 0$ ; $V_{CE} = 30\text{ V}$	–	–	1	$\mu\text{A}$
		$I_B = 0$ ; $V_{CE} = 30\text{ V}$ ; $T_j = 150\text{ °C}$	–	–	50	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0$ ; $V_{EB} = 5\text{ V}$	–	–	400	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_C = 5\text{ mA}$ ; $V_{CE} = 5\text{ V}$	30	–	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}$ ; $I_B = 0.5\text{ mA}$	–	–	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 100\text{ }\mu\text{A}$ ; $V_{CE} = 5\text{ V}$	–	1.1	0.8	V
$V_{i(on)}$	input-on voltage	$I_C = 10\text{ mA}$ ; $V_{CE} = 0.3\text{ V}$	2.5	1.8	–	V
R1	input resistor		7	10	13	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
$C_c$	collector capacitance	$I_E = I_B = 0$ ; $V_{CB} = 10\text{ V}$ ; $f = 1\text{ MHz}$	–	–	2.5	pF

NPN resistor-equipped transistor

PDTC114ES



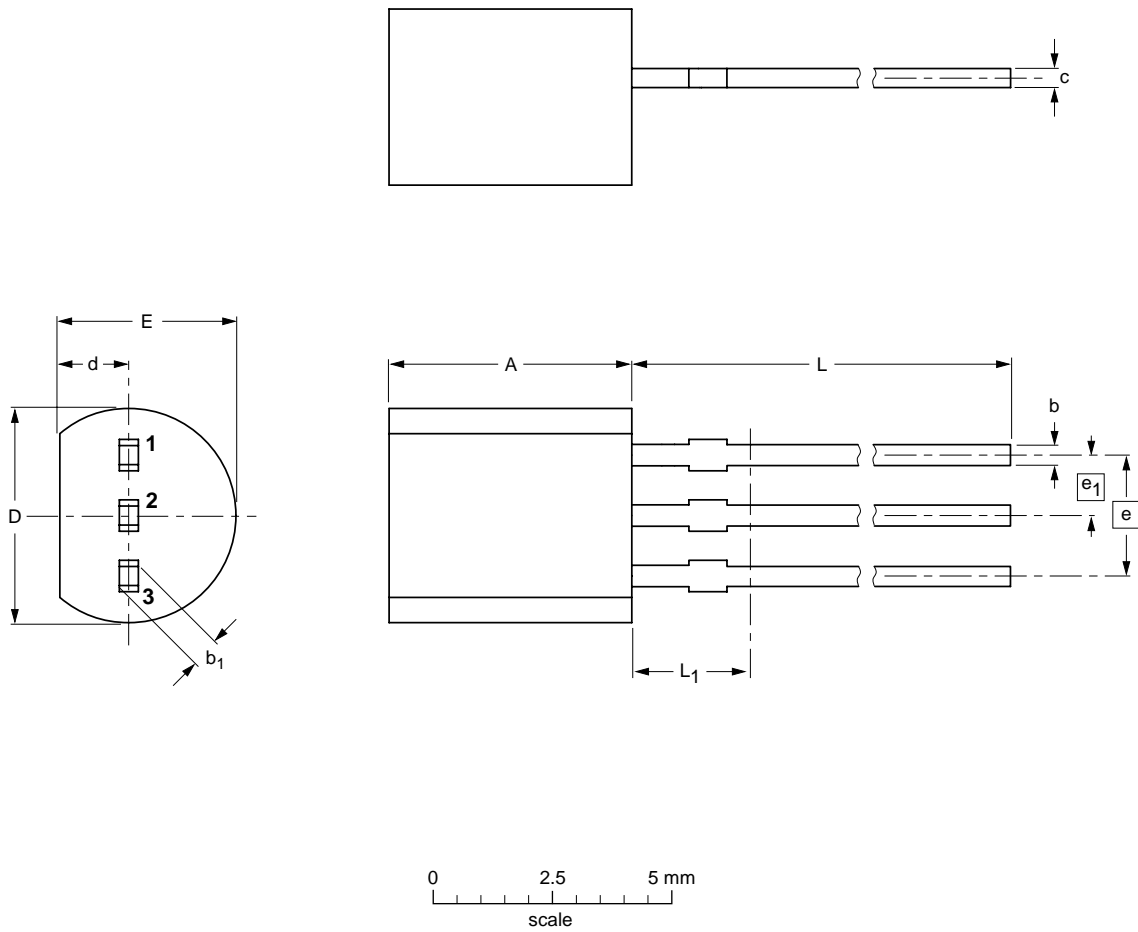
NPN resistor-equipped transistor

PDTC114ES

PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b <sub>1</sub>	c	D	d	E	e	e <sub>1</sub>	L	L <sub>1</sub> <sup>(1)</sup>
mm	5.2 5.0	0.48 0.40	0.66 0.56	0.45 0.40	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ		
SOT54		TO-92	SC-43		97-02-28

## NPN resistor-equipped transistor

PDTC114ES

**DEFINITIONS**

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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NPN resistor-equipped transistor

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**Australia:** 34 Waterloo Road, NORTH RYDE, NSW 2113, Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

**Austria:** Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010, Fax. +43 160 101 1210

**Belarus:** Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6, 220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

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**Bulgaria:** Philips Bulgaria Ltd., Energoproject, 15th floor, 51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 689 211, Fax. +359 2 689 102

**Canada:** PHILIPS SEMICONDUCTORS/COMPONENTS, Tel. +1 800 234 7381

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**Denmark:** Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S, Tel. +45 32 88 2636, Fax. +45 31 57 0044

**Finland:** Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615800, Fax. +358 9 61580920

**France:** 51 Rue Carnot, BP317, 92156 SURESNES Cedex, Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

**Germany:** Hammerbrookstraße 69, D-20097 HAMBURG, Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

**Greece:** No. 15, 25th March Street, GR 17778 TAVROS/ATHENS, Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

**Hungary:** see Austria

**India:** Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025, Tel. +91 22 493 8541, Fax. +91 22 493 0966

**Indonesia:** PT Philips Development Corporation, Semiconductors Division, Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510, Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

**Ireland:** Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

**Israel:** RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

**Italy:** PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3, 20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

**Japan:** Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

**Korea:** Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL, Tel. +82 2 709 1412, Fax. +82 2 709 1415

**Malaysia:** No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR, Tel. +60 3 750 5214, Fax. +60 3 757 4880

**Mexico:** 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905, Tel. +9-5 800 234 7381

**Middle East:** see Italy

**Netherlands:** Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB, Tel. +31 40 27 82785, Fax. +31 40 27 88399

**New Zealand:** 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +64 9 849 4160, Fax. +64 9 849 7811

**Norway:** Box 1, Manglerud 0612, OSLO, Tel. +47 22 74 8000, Fax. +47 22 74 8341

**Pakistan:** see Singapore

**Philippines:** Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

**Poland:** Ul. Lukiska 10, PL 04-123 WARSZAWA, Tel. +48 22 612 2831, Fax. +48 22 612 2327

**Portugal:** see Spain

**Romania:** see Italy

**Russia:** Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW, Tel. +7 095 755 6918, Fax. +7 095 755 6919

**Singapore:** Lorong 1, Toa Payoh, SINGAPORE 319762, Tel. +65 350 2538, Fax. +65 251 6500

**Slovakia:** see Austria

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**South America:** Al. Vicente Pinzon, 173, 6th floor, 04547-130 SÃO PAULO, SP, Brazil, Tel. +55 11 821 2333, Fax. +55 11 821 2382

**Spain:** Balmes 22, 08007 BARCELONA, Tel. +34 93 301 6312, Fax. +34 93 301 4107

**Sweden:** Kottbygatan 7, Akalla, S-16485 STOCKHOLM, Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

**Switzerland:** Allmendstrasse 140, CH-8027 ZÜRICH, Tel. +41 1 488 2741 Fax. +41 1 488 3263

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**Ukraine:** PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7, 252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

**United Kingdom:** Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

**United States:** 811 East Arques Avenue, SUNNYVALE, CA 94088-3409, Tel. +1 800 234 7381

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**For all other countries apply to:** Philips Semiconductors, International Marketing & Sales Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

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